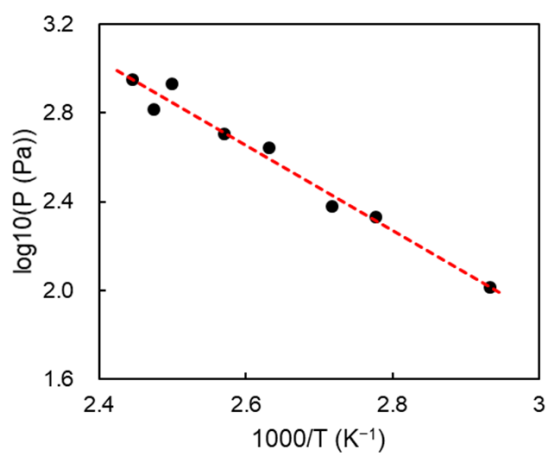
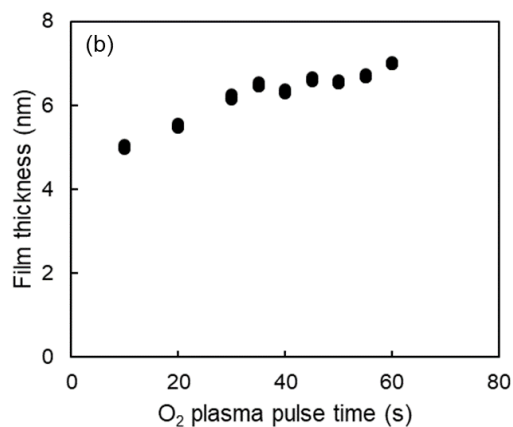
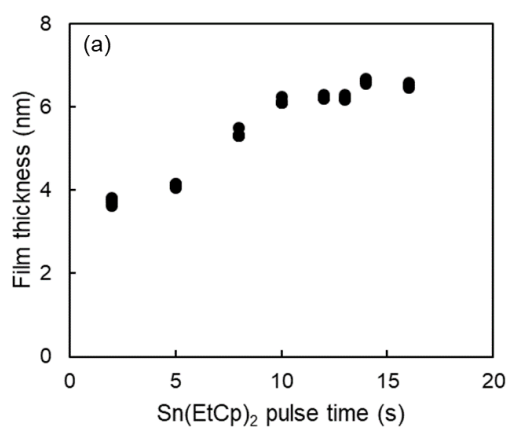


# Atomic Layer Deposition of Tin Oxide Thin Films Using a New Liquid Precursor Bis(ethylcyclopentadienyl) Tin

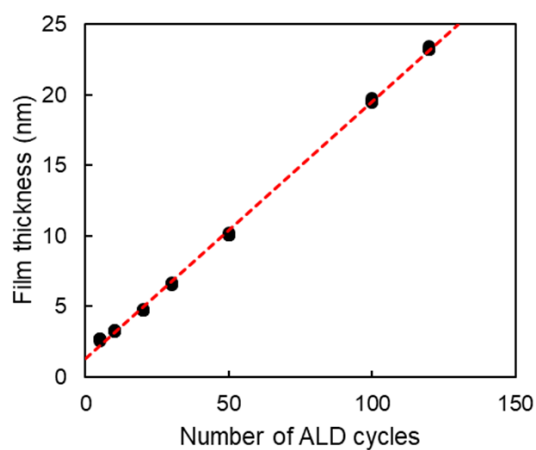
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The Clausius-Clapeyron plot for Sn(EtCp)<sub>2</sub>.



SnO<sub>x</sub> film thickness as a function of (a) Sn(EtCp)<sub>2</sub> pulse time and (b) O<sub>2</sub> plasma pulse time deposited at 200 °C. The number of ALD cycles was 30.



SnO<sub>x</sub> film thickness as a function of ALD cycles. The ALD conditions were a Sn(EtCp)<sub>2</sub> pulse time of 14 s, an O<sub>2</sub> plasma pulse time of 45 s, and a growth temperature of 200 °C.